SN74ALVC14 HEX SCHMITT-TRIGGER INVERTER

SCES107E - JULY 1997 - REVISED AUGUST 1999

- EPIC[™] (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

D, DGV, OR PW PACKAGE

description

This hex Schmitt-trigger inverter is designed for 2.3-V to 3.6-V V_{CC} operation.

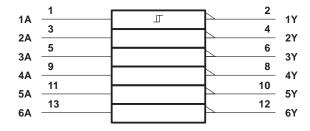
The SN74ALVC14 contains six independent inverters and performs the Boolean function $Y = \overline{A}$.

The SN74ALVC14 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE (each gate)

INPUT A	OUTPUT Y
Н	L
L	Н

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each inverter (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}		–0.5 V to 4.6 V
Input voltage range, V _I (see Note 1)		–0.5 V to 4.6 V
Output voltage range, V _O (see Notes 1 and 2)		. -0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)		
Output clamp current, I_{OK} ($V_O < 0$)		
Continuous output current, IO		±50 mA
Continuous current through V _{CC} or GND		±100 mA
Package thermal impedance, θ _{JA} (see Note 3):	: D package	127°C/W
,	DGV package	182°C/W
	PW package	170°C/W
Storage temperature range, T _{stg}		–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V _{CC} Supply voltage		2.3	3.6	V	
V _I Input voltage		0	Vcc	V	
Vo	Output voltage		0	Vcc	V
IOH High-level output current		V _{CC} = 2.3 V		-12	
	V _{CC} = 2.7 V		-12	mA	
		V _{CC} = 3 V		-24	
		V _{CC} = 2.3 V		12	
loL	IOL Low-level output current	V _{CC} = 2.7 V		12	mA
		V _{CC} = 3 V		24	
TA	Operating free-air temperature		-40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



SCES107E - JULY 1997 - REVISED AUGUST 1999

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST C	CONDITIONS	VCC	MIN	TYP [†]	MAX	UNIT	
			2.3 V	0.7		1.7		
V _{T+}			2.7 V	0.8		2	V	
Positive-going threshold			3 V	0.8		2	V	
			3.6 V	0.8		2		
			2.3 V	0.35		1.3		
V _T – Negative-going			2.7 V	0.4		1.4	V	
threshold			3 V	0.6		1.5	V	
			3.6 V	0.8		1.8		
			2.3 V	0.3		1		
ΔVT			2.7 V	0.3		1.1	V	
Hysteresis (V _{T+} – V _T _)			3 V	0.3		1.2	V	
(17 1-7			3.6 V	0.3		1.2		
	I _{OH} = -100 μA		2.3 V to 3.6 V	V _{CC} -0.	2			
	$I_{OH} = -6 \text{ mA}$		2.3 V	2				
Vari	I _{OH} = -12 mA		2.3 V	1.7			V	
VOH			2.7 V	2.2				
		3 V	2.4					
	I _{OH} = -24 mA		3 V	2				
	I _{OL} = 100 μA		2.3 V to 3.6 V			0.2		
	I _{OL} = 6 mA		2.3 V			0.4		
V _{OL}	lo 12 mΛ	10 1				0.7	V	
	I _{OL} = 12 mA		2.7 V			0.4		
	I _{OL} = 24 mA		3 V			0.55		
lį	$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ	
Icc	$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			10	μΑ	
ΔlCC	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ	
Ci	$V_I = V_{CC}$ or GND		3.3 V		4		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

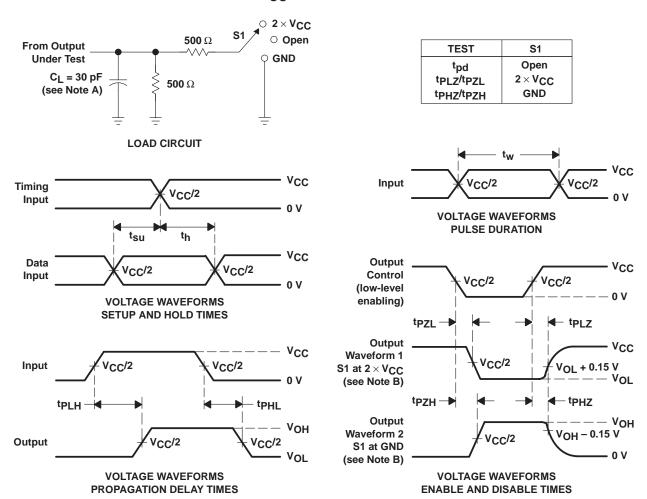
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(1141 01)		MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	А	Υ	1	3.7		3.9	1	3.4	ns

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS		V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
				TYP	TYP	ONII
C _{pd}	Power dissipation capacitance per inverter	C _L = 0,	f = 10 MHz	27	31	pF



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 V \pm 0.2 V$

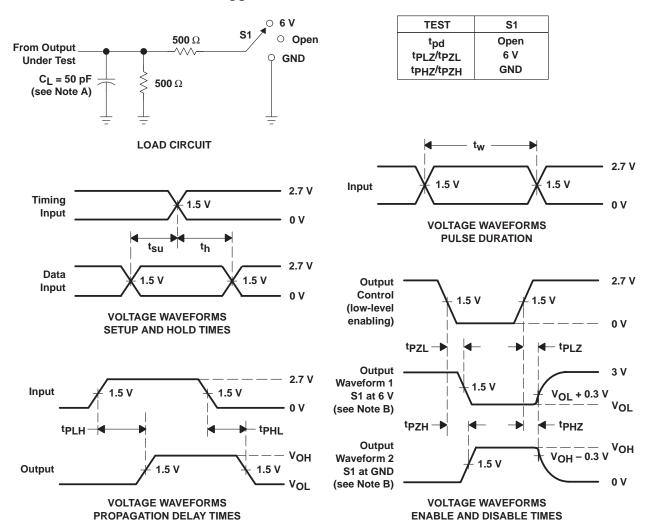


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z $_{O}$ = 50 $\Omega,\,t_{f}\leq$ 2 ns. $t_{f}\leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

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